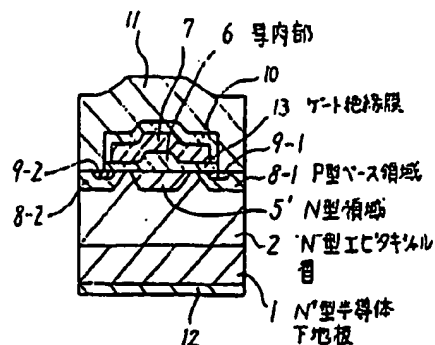


Patent Abstracts of Japan

TITLE : VERTICAL INSULATED GATE FIELD EFFECT TRANSISTOR



COPYRIGHT: (C)1989,JPO&Japio